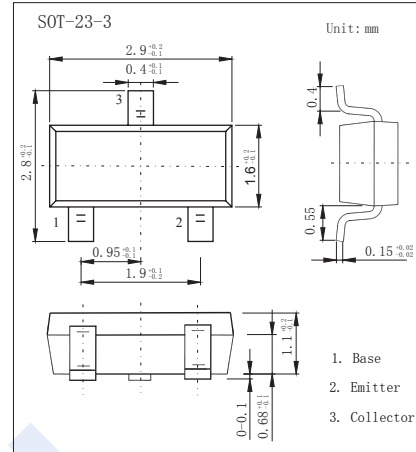


PNP Transistors

2SB792A-HF

■ Features

- High collector to emitter voltage V_{CE0} .
- Low noise voltage NV
- Complimentary to 2SD814A-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-185	V
Collector - Emitter Voltage	V_{CEO}	-185	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-50	mA
Collector Current - Pulse	I_{CP}	-100	
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -100 \mu\text{A}, I_E = 0$	-185			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{mA}, I_B = 0$	-185			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -120 \text{V}, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 \text{V}, I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -30 \text{mA}, I_B = -3 \text{mA}$			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -30 \text{mA}, I_B = -3 \text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -5 \text{V}, I_C = -10 \text{mA}$	130		330	
Noise voltage	NV	$V_{CE} = -10 \text{V}, I_C = -1 \text{mA}, G_v = 80 \text{dB}, R_g = 100 \text{k}\Omega, \text{Function} = \text{FLAT}$		150		mV
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{V}, I_E = 0, f = 1 \text{MHz}$		4		pF
Transition frequency	f_T	$V_{CE} = -10 \text{V}, I_E = 10 \text{mA}, f = 200 \text{MHz}$		200		MHz

■ Classification of h_{FE}

Type	2SB792A-R-HF	2SB792A-S-HF
Range	130-220	185-330
Marking	2FR _F	2FS _F

PNP Transistors

2SB792A-HF

■ Typical Characteristics

